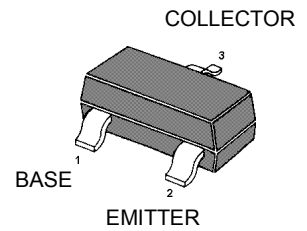




2SD882 Power Transistor

The transistor is subdivided into four groups, R, Q, P and E, according to its DC current gain.

MARKING:D882



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Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

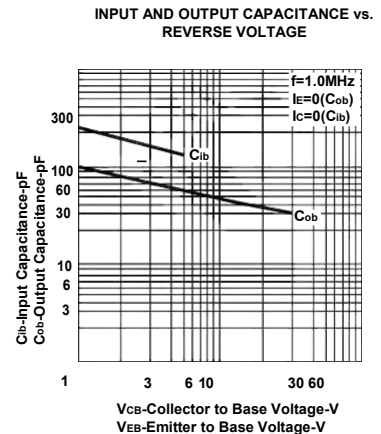
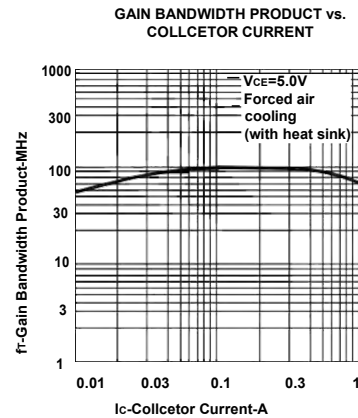
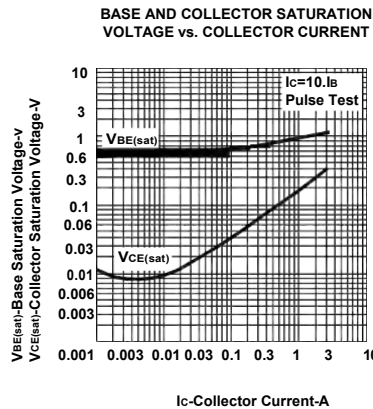
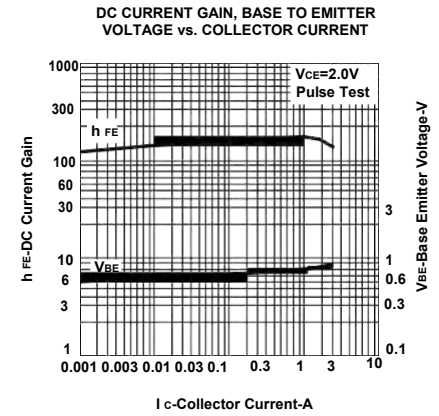
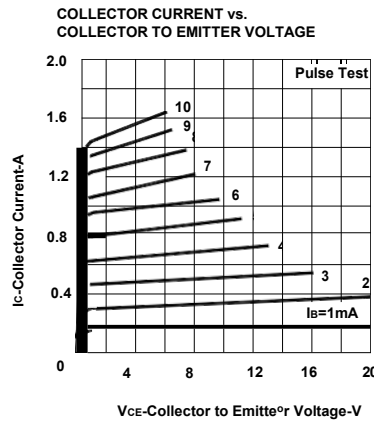
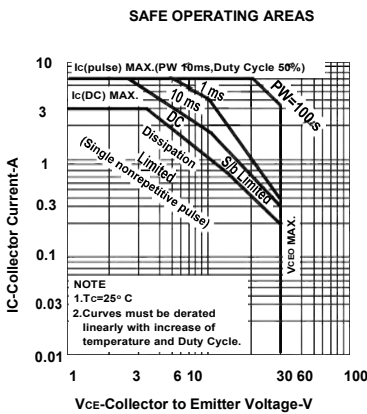
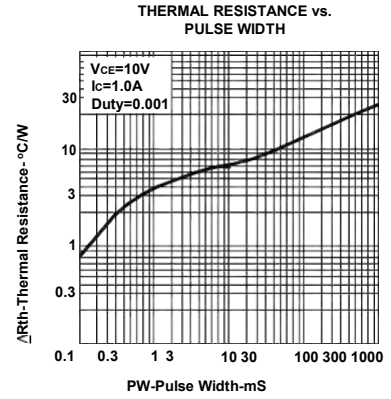
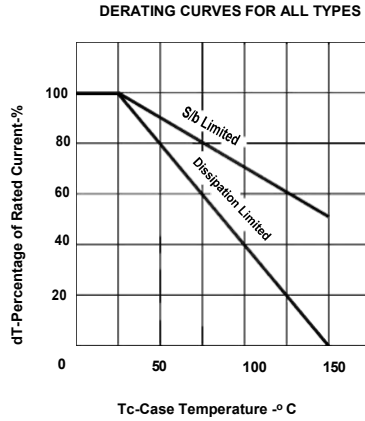
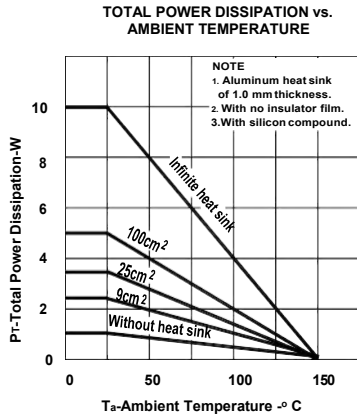
Parameter	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2	A
Total power dissipation ($T_a = 25^\circ\text{C}$)	P_{tot}	0.5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$	h_{FE}	30	-	-	-
at $V_{CE} = 2\text{ V}$, $I_C = 1\text{ A}$ Current Gain Group	R h_{FE}	60	-	120	-
	Q h_{FE}	100	-	200	-
	P h_{FE}	160	-	320	-
	E h_{FE}	200	-	400	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	1	μA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	-	1	μA
Collector Emitter Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$	$V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$	$V_{BE(sat)}$	-	-	2	V
Gain Bandwidth Product at $V_{CE} = 5\text{ V}$, $I_C = 0.1\text{ A}$	f_T	-	90	-	MHz
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	45	-	pF



TYPICAL CHARACTERISTICS (Ta=25°C)

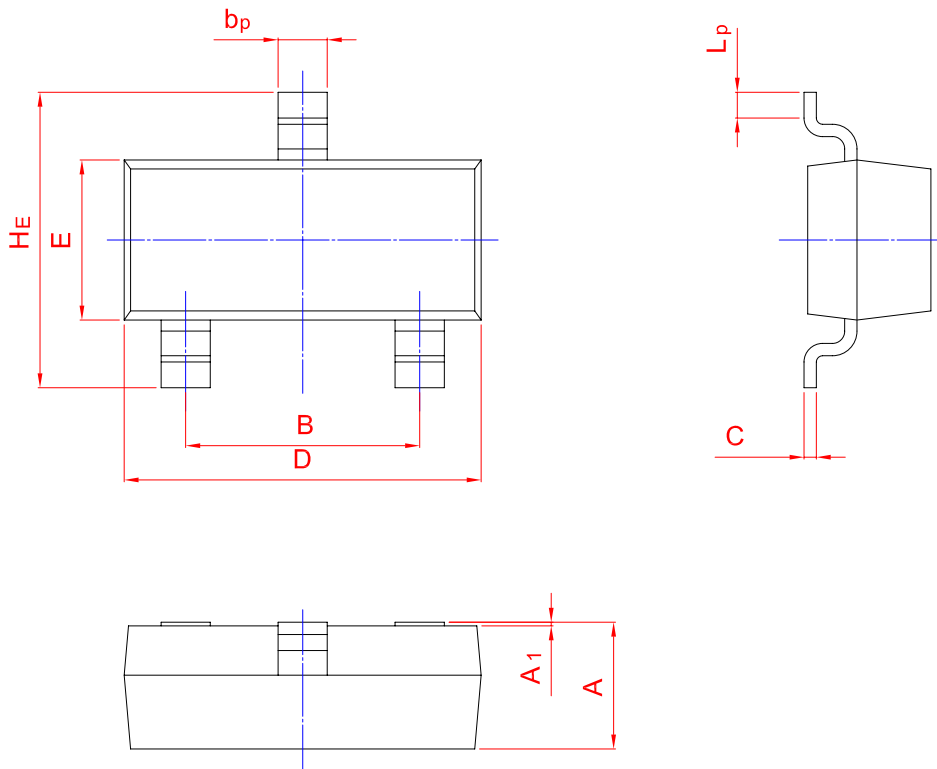
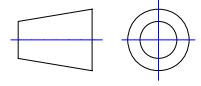




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20